



SANYO Semiconductors

DATA SHEET

CPH3148 — PNP Epitaxial Planar Silicon Transistor

High-Voltage Switching Applications

Applications

- DC / DC converters, relay drivers, lamp drivers, motor drivers.

Features

- Adoption of FBET, MBIT processes.
- Large current capacitance.
- Low collector-to-emitter saturation voltage.
- High-speed switching.
- Ultrasmall package permitting applied sets to be small and slim (mounting height: 0.9mm).
- High allowable power dissipation.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		-100	V
Collector-to-Emitter Voltage	VCEs		-100	V
Collector-to-Emitter Voltage	VCEO		-100	V
Emitter-to-Base Voltage	VEBO		-7	V
Collector Current	IC		-2	A
Collector Current (Pulse)	ICP		-3	A
Base Current	IB		-400	mA
Collector Dissipation	PC	Mounted on a ceramic board (600mm ² ×0.8mm)	0.9	W
Junction Temperature	TJ		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	ICBO	V _{CB} =-80V, I _E =0A			-1	μA
Emitter Cutoff Current	IEBO	V _{EB} =-4V, I _C =0A			-1	μA
DC Current Gain	h _{FE}	V _{CE} =-5V, I _C =-100mA	200		400	
Gain-Bandwidth Product	f _T	V _{CE} =-10V, I _C =-500mA		260		MHz
Output Capacitance	Cob	V _{CB} =-10V, f=1MHz		20		pF

Marking : BP

Continued on next page.

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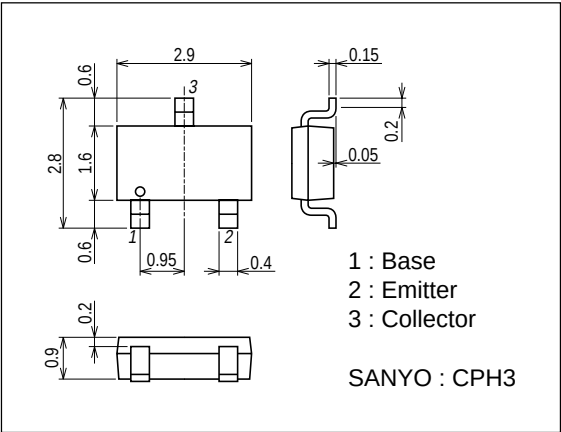
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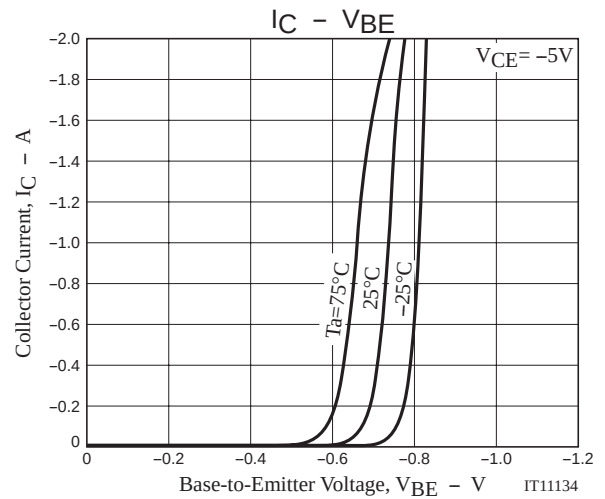
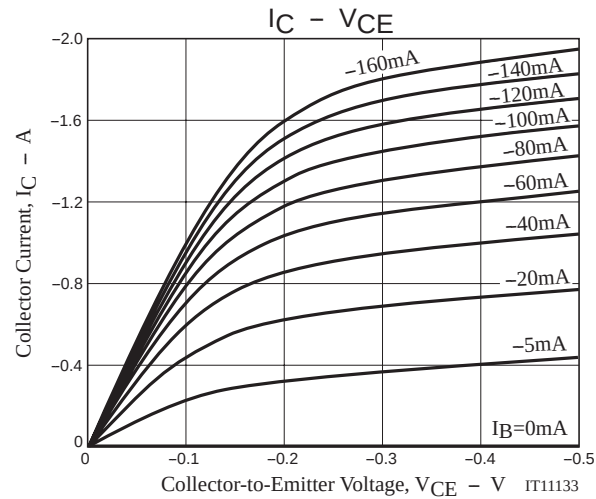
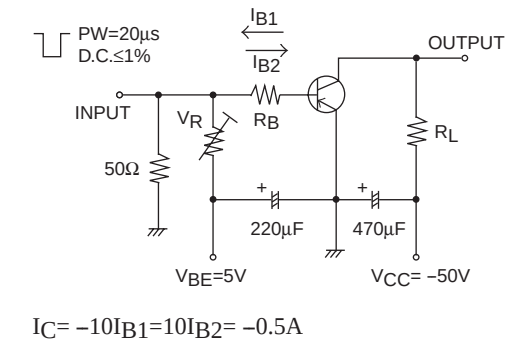
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -1A, I_B = -100mA$		-120	-240	mV
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -1A, I_B = -100mA$		-0.85	-1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -10\mu A, I_E = 0A$	-100			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CES}$	$I_C = -100\mu A, R_{BE} = 0\Omega$	-100			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1mA, R_{BE} = \infty$	-100			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0A$	-7			V
Turn-ON Time	t_{on}	See specified Test Circuit.		40		ns
Storage Time	t_{stg}	See specified Test Circuit.		600		ns
Fall Time	t_f	See specified Test Circuit.		30		ns

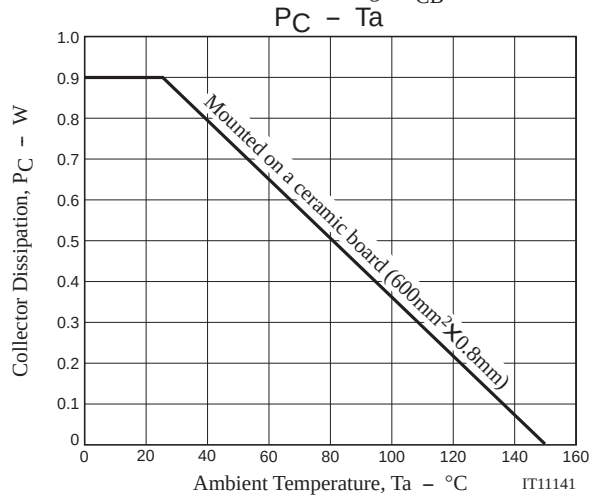
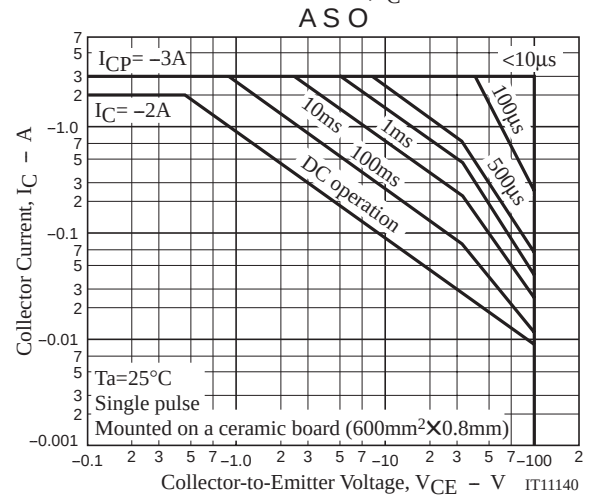
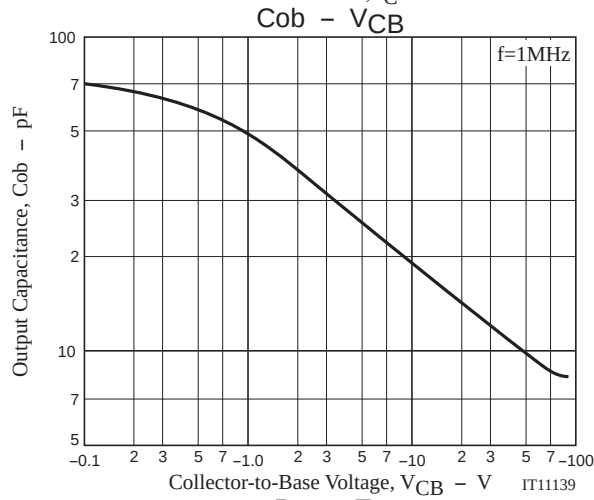
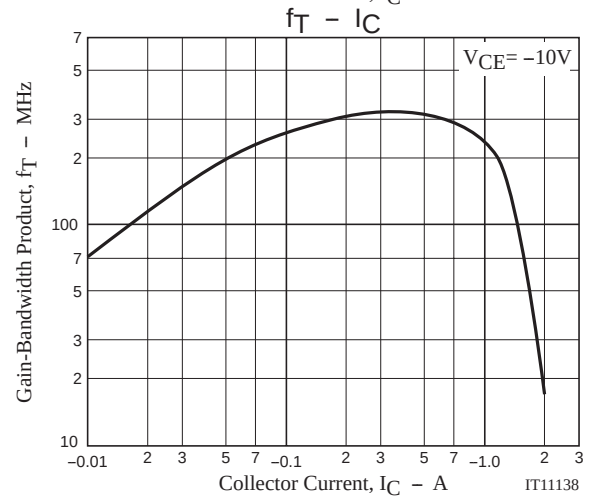
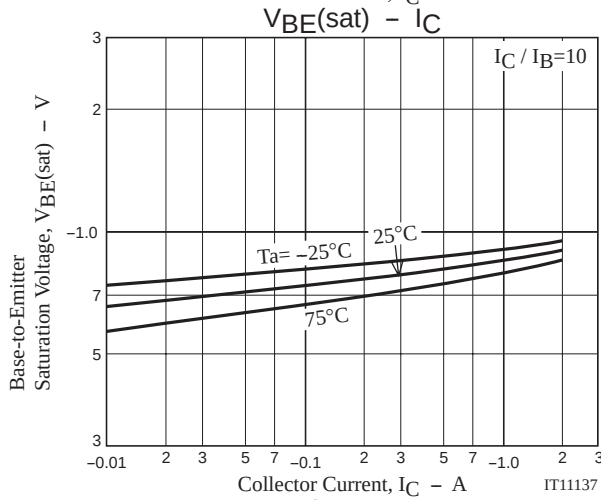
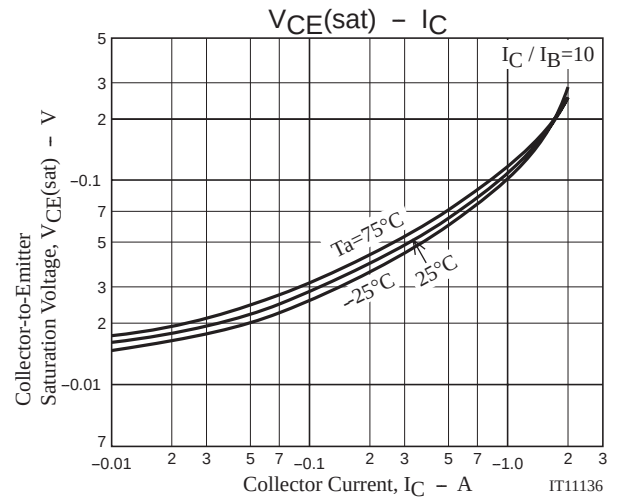
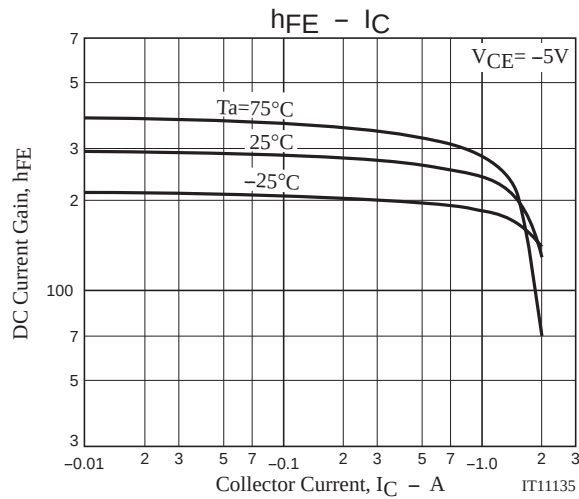
Package Dimensions

unit : mm (typ)
7015A-003



Switching Time Test Circuit





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